

FQPF17N40



April 2000

QFET™

## FQPF17N40

### 400V N-Channel MOSFET

#### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply, electronic lamp ballast based on half bridge.

#### Features

- 9.5A, 400V,  $R_{DS(on)} = 0.27\Omega$  @  $V_{GS} = 10\text{ V}$
- Low gate charge ( typical 45 nC)
- Low Crss ( typical 30 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



#### Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	FQPF17N40	Units
$V_{DSS}$	Drain-Source Voltage	400	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ )	9.5	A
	- Continuous ( $T_C = 100^\circ\text{C}$ )	6.0	A
$I_{DM}$	Drain Current - Pulsed	(Note 1)	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	mJ
$I_{AR}$	Avalanche Current	(Note 1)	A
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$	(Note 3)	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ )	56	W
	- Derate above $25^\circ\text{C}$	0.45	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

#### Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	2.23	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C}/\text{W}$

## Electrical Characteristics

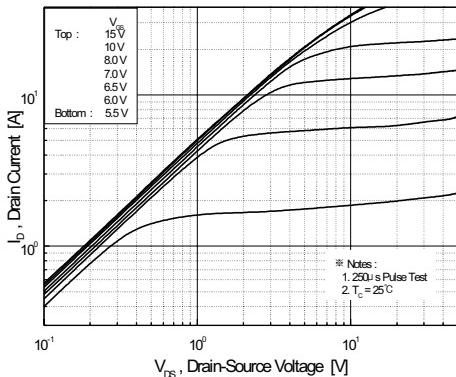
$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}} = 0 \text{ V}, I_D = 250 \mu\text{A}$	400	--	--	V
$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.44	--	$\text{V}/^\circ\text{C}$
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}} = 400 \text{ V}, V_{\text{GS}} = 0 \text{ V}$	--	--	1	$\mu\text{A}$
		$V_{\text{DS}} = 320 \text{ V}, T_C = 125^\circ\text{C}$	--	--	10	$\mu\text{A}$
$I_{\text{GSSF}}$	Gate-Body Leakage Current, Forward	$V_{\text{GS}} = 30 \text{ V}, V_{\text{DS}} = 0 \text{ V}$	--	--	100	nA
$I_{\text{GSSR}}$	Gate-Body Leakage Current, Reverse	$V_{\text{GS}} = -30 \text{ V}, V_{\text{DS}} = 0 \text{ V}$	--	--	-100	nA
<b>On Characteristics</b>						
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250 \mu\text{A}$	3.0	--	5.0	V
$R_{\text{DS(on)}}$	Static Drain-Source On-Resistance	$V_{\text{GS}} = 10 \text{ V}, I_D = 4.75 \text{ A}$	--	0.21	0.27	$\Omega$
$g_{\text{FS}}$	Forward Transconductance	$V_{\text{DS}} = 50 \text{ V}, I_D = 4.75 \text{ A}$ (Note 4)	--	10	--	S
<b>Dynamic Characteristics</b>						
$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}} = 25 \text{ V}, V_{\text{GS}} = 0 \text{ V}, f = 1.0 \text{ MHz}$	--	1800	2300	pF
$C_{\text{oss}}$	Output Capacitance		--	270	350	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance		--	30	40	pF
<b>Switching Characteristics</b>						
$t_{\text{d(on)}}$	Turn-On Delay Time	$V_{\text{DD}} = 200 \text{ V}, I_D = 17.2 \text{ A}, R_G = 25 \Omega$	--	40	90	ns
$t_r$	Turn-On Rise Time		--	185	380	ns
$t_{\text{d(off)}}$	Turn-Off Delay Time		--	90	190	ns
$t_f$	Turn-Off Fall Time		--	105	220	ns
$Q_g$	Total Gate Charge	$V_{\text{DS}} = 320 \text{ V}, I_D = 17.2 \text{ A}, V_{\text{GS}} = 10 \text{ V}$	--	45	60	nC
$Q_{\text{gs}}$	Gate-Source Charge		--	11.4	--	nC
$Q_{\text{gd}}$	Gate-Drain Charge		--	21.7	--	nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	9.5	A	
$I_{\text{SM}}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	38	A	
$V_{\text{SD}}$	Drain-Source Diode Forward Voltage	$V_{\text{GS}} = 0 \text{ V}, I_S = 9.5 \text{ A}$	--	--	1.5	V
$t_{\text{rr}}$	Reverse Recovery Time	$V_{\text{GS}} = 0 \text{ V}, I_S = 17.2 \text{ A}, dI_F / dt = 100 \text{ A}/\mu\text{s}$	--	290	--	ns
$Q_{\text{rr}}$	Reverse Recovery Charge		--	2.5	--	$\mu\text{C}$

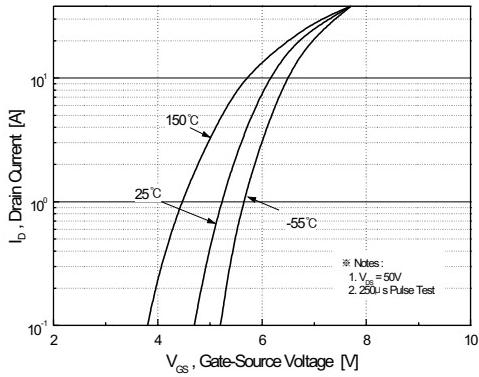
**Notes:**

- Repetitive Rating : Pulse width limited by maximum junction temperature
- $L = 19.4\text{mH}, I_{AS} = 9.5\text{A}, V_{DD} = 50\text{V}, R_G = 25 \Omega$ , Starting  $T_J = 25^\circ\text{C}$
- $I_{SP} \leq 17.2\text{A}, d/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq \text{BV}_{\text{DSS}}$ , Starting  $T_J = 25^\circ\text{C}$
- Pulse Test : Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$
- Essentially independent of operating temperature

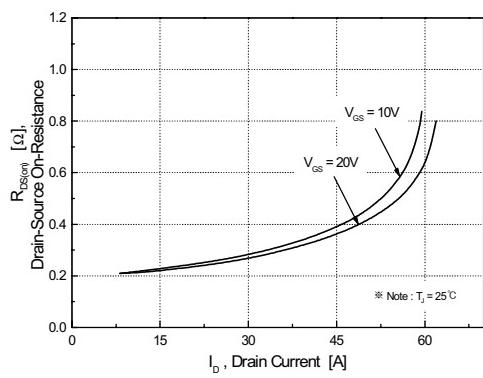
## Typical Characteristics



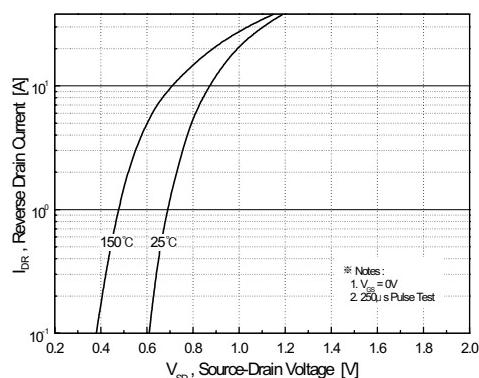
**Figure 1. On-Region Characteristics**



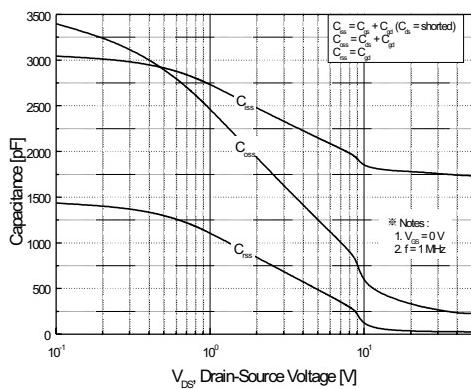
**Figure 2. Transfer Characteristics**



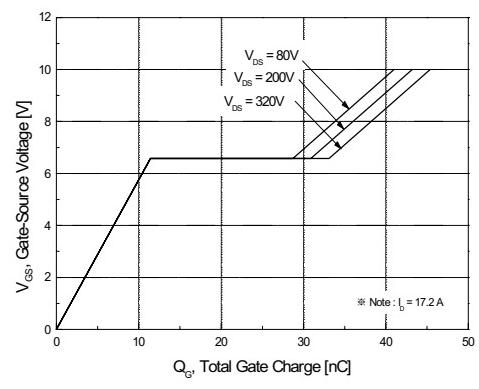
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**

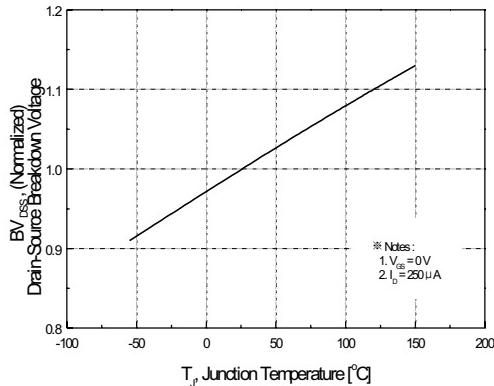


**Figure 5. Capacitance Characteristics**

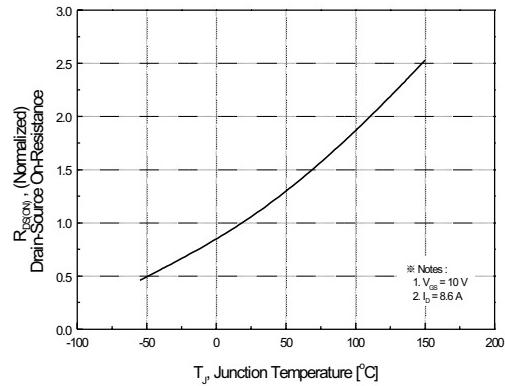


**Figure 6. Gate Charge Characteristics**

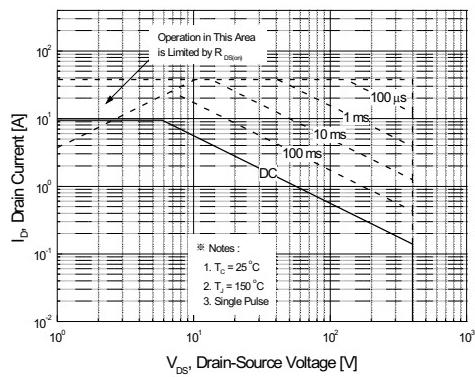
## Typical Characteristics (Continued)



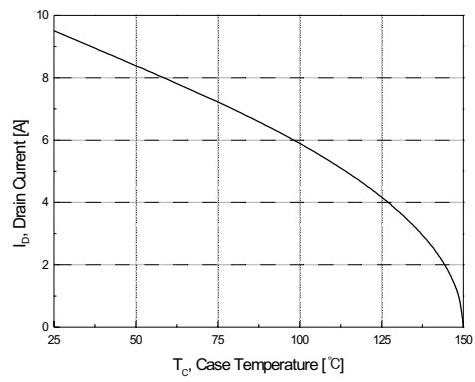
**Figure 7. Breakdown Voltage Variation vs. Temperature**



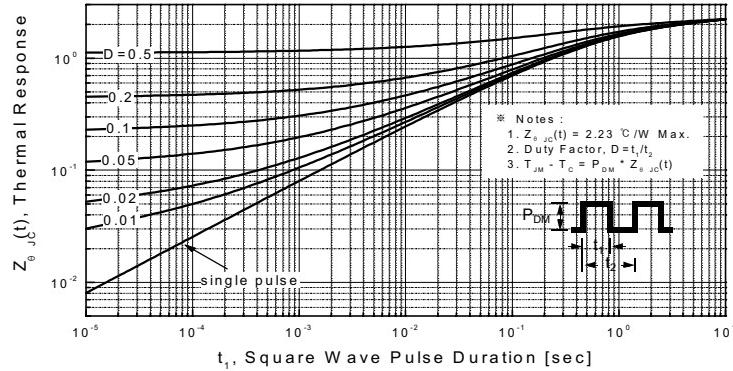
**Figure 8. On-Resistance Variation vs. Temperature**



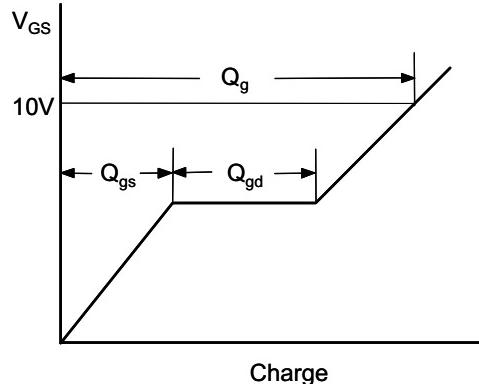
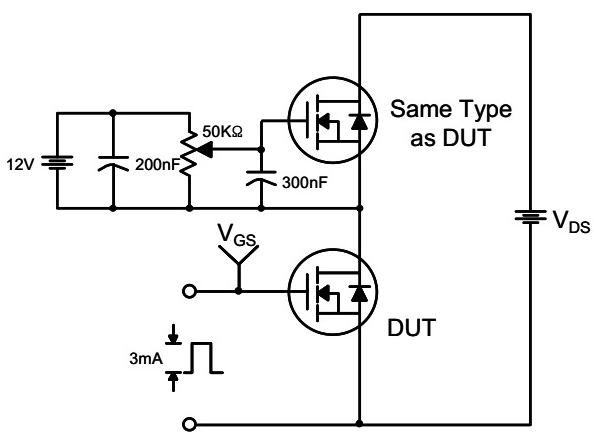
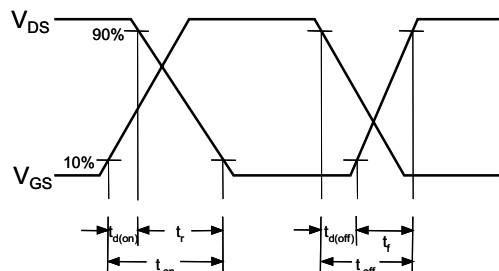
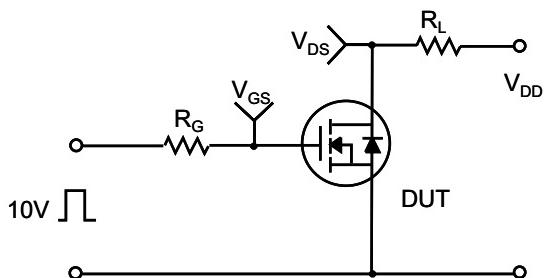
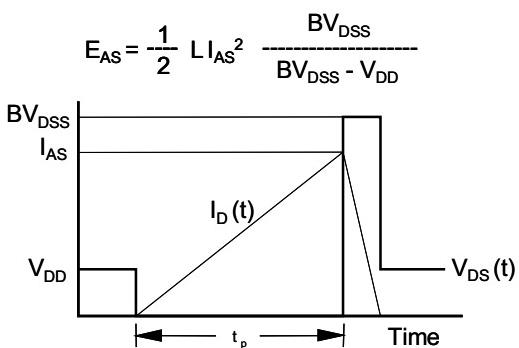
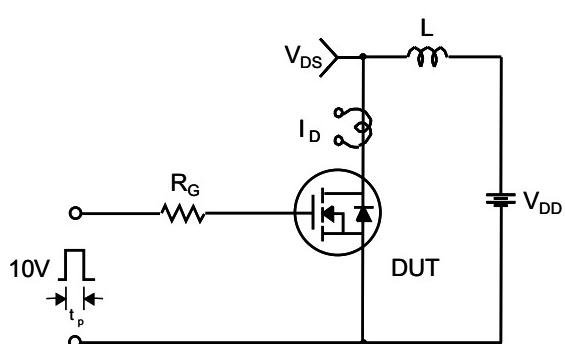
**Figure 9. Maximum Safe Operating Area.**



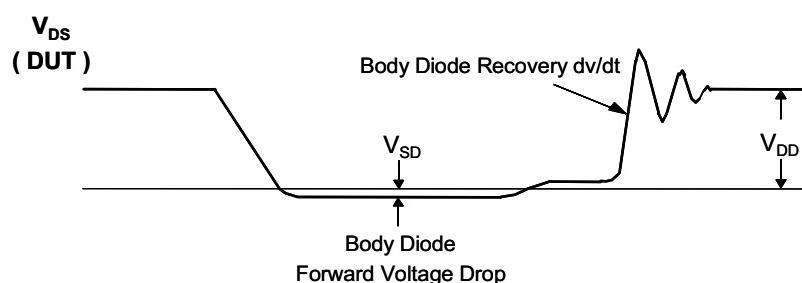
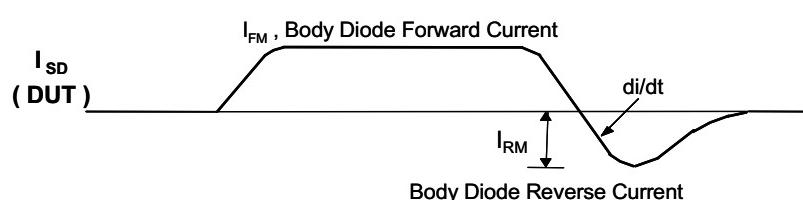
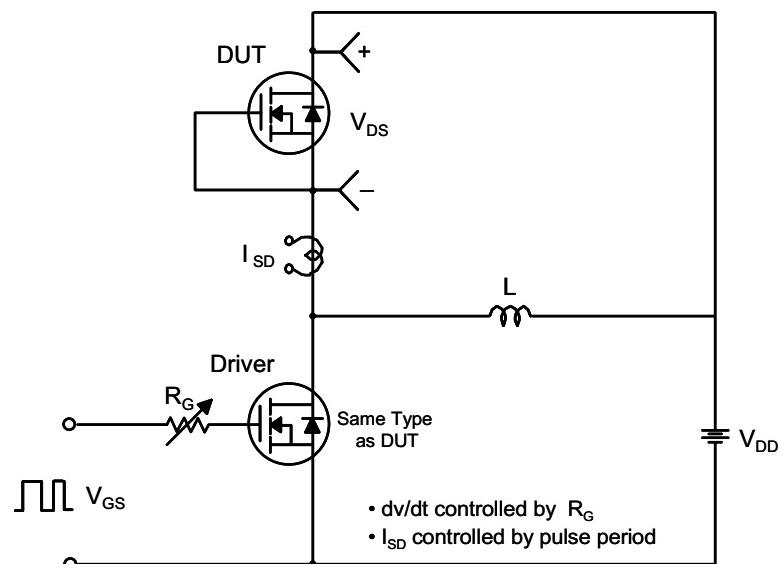
**Figure 10. Maximum Drain Current vs Case Temperature.**

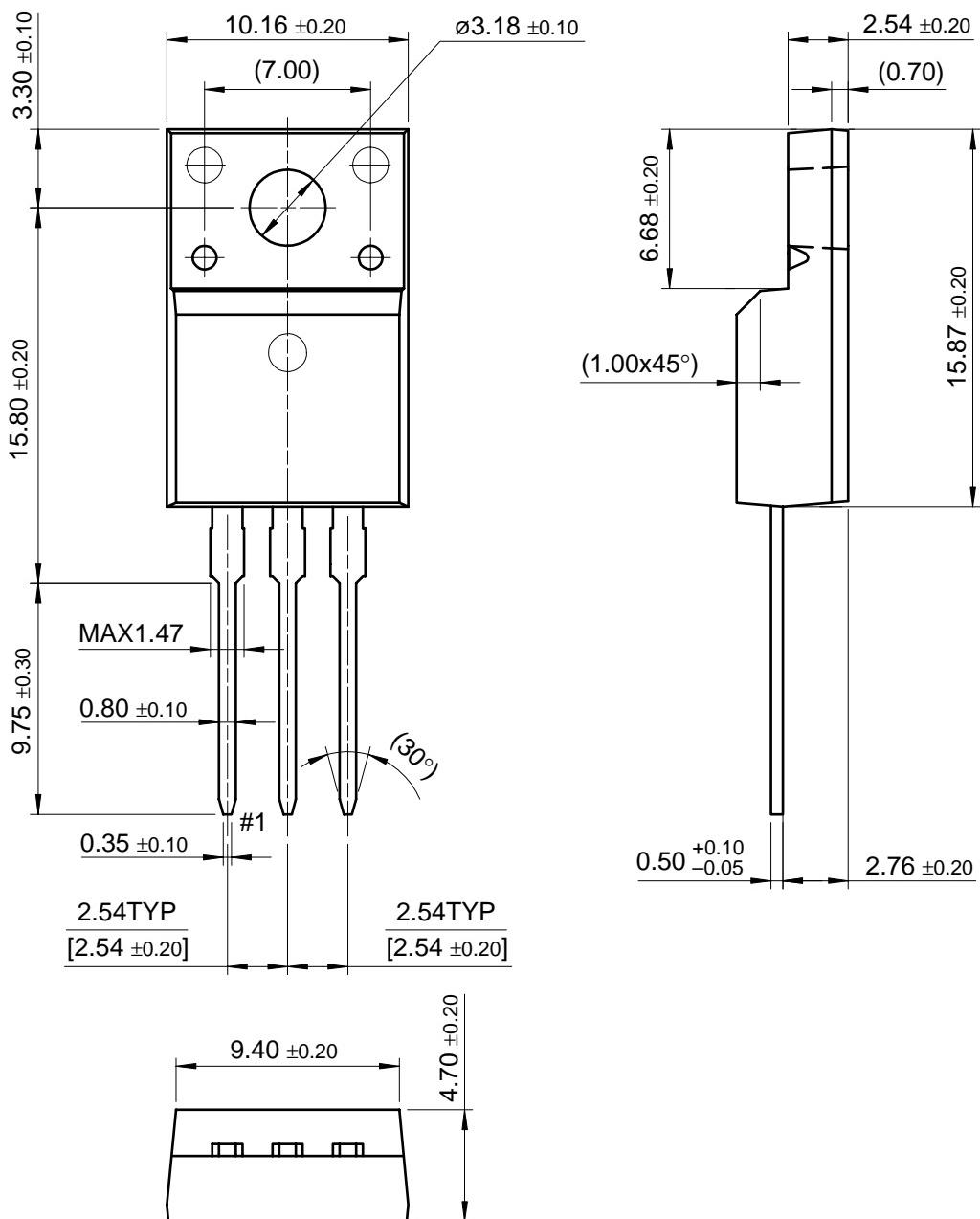


**Figure 11. Transient Thermal Response Curve**

**Gate Charge Test Circuit & Waveform****Resistive Switching Test Circuit & Waveforms****Unclamped Inductive Switching Test Circuit & Waveforms**

## Peak Diode Recovery dv/dt Test Circuit &amp; Waveforms



**Package Dimensions****TO-220F**

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